

# **isc** Silicon NPN Power Transistor

# **BU606D**

## **DESCRIPTION**

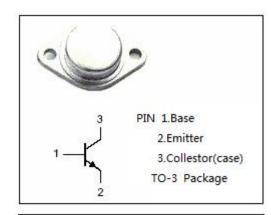
- · Fast Switching Speed-
- : t<sub>f</sub>= 0.75 μ s(Max)
- · Low Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 1.0V(Max)@ I<sub>C</sub>= 5A
- · Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

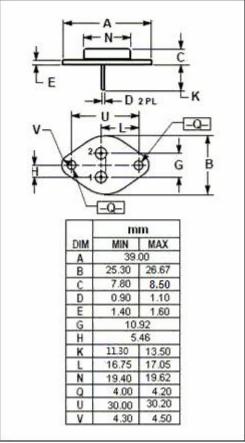
## **APPLICATIONS**

 Designed for use in horizontal deflection output stages of TV's and CRT's

## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	400	٧
V <sub>CEV</sub>	Collector-Emitter Voltage	400	V
V <sub>CEO</sub>	Collector-Emitter Voltage	200	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ic	Collector Current-Continuous	7	А
Іср	Collector Current-Peak Repetitive	10	А
I <sub>CP</sub>	Collector Current- Peak (10ms)	15	А
I <sub>B</sub>	Base Current	4	Α
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	90	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ;I <sub>B</sub> = 0	200			V
V <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 200mA; I <sub>C</sub> = 0	6.0			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.65A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.65A			1.2	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 400V; V <sub>BE</sub> = 0 V <sub>CE</sub> =250V; V <sub>BE</sub> = 0 V <sub>CE</sub> =250V; V <sub>BE</sub> = 0;T <sub>C</sub> = 150℃			5.0 0.1 1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			400	mA
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V, f <sub>test</sub> = 20MHz	10			MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		80		pF
t <sub>f</sub>	Fall Time	$I_{C}$ = 5A; $I_{B1}$ = - $I_{B2}$ = 0.5A, L= 150 $\mu$ H $V_{CC}$ = 40V			0.75	μS

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